

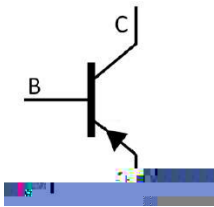
WR0<5+U, M M E SQS æ M y s ll 1 Silicon PNP transistor in a TO-92(R) Plastic Package.

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High voltage, complementary to BC546.

$$\tilde{\mathbb{E}}_0^{\text{c}} \quad \omega \approx 3 \tilde{A} H$$

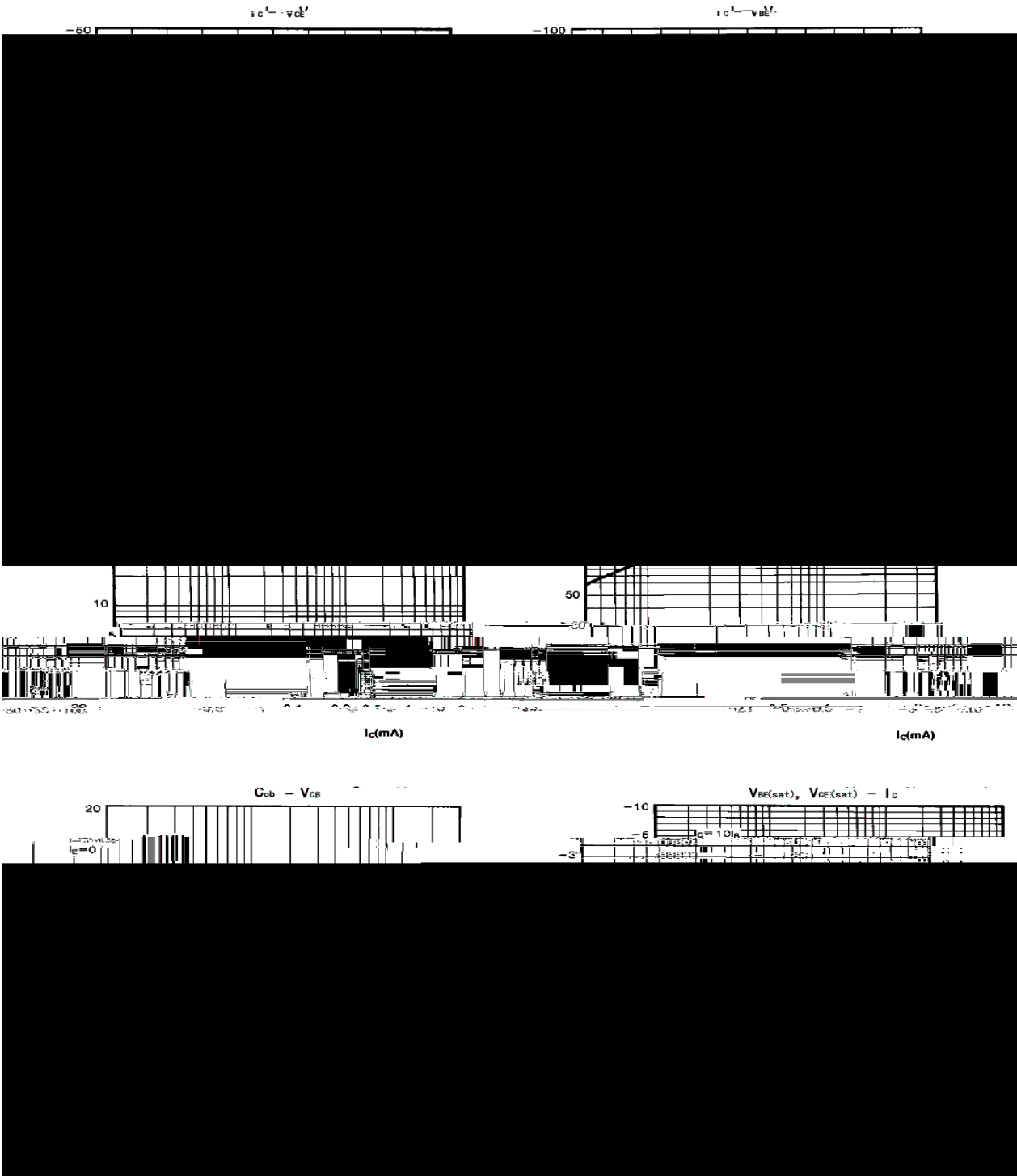
General purpose and switching application.

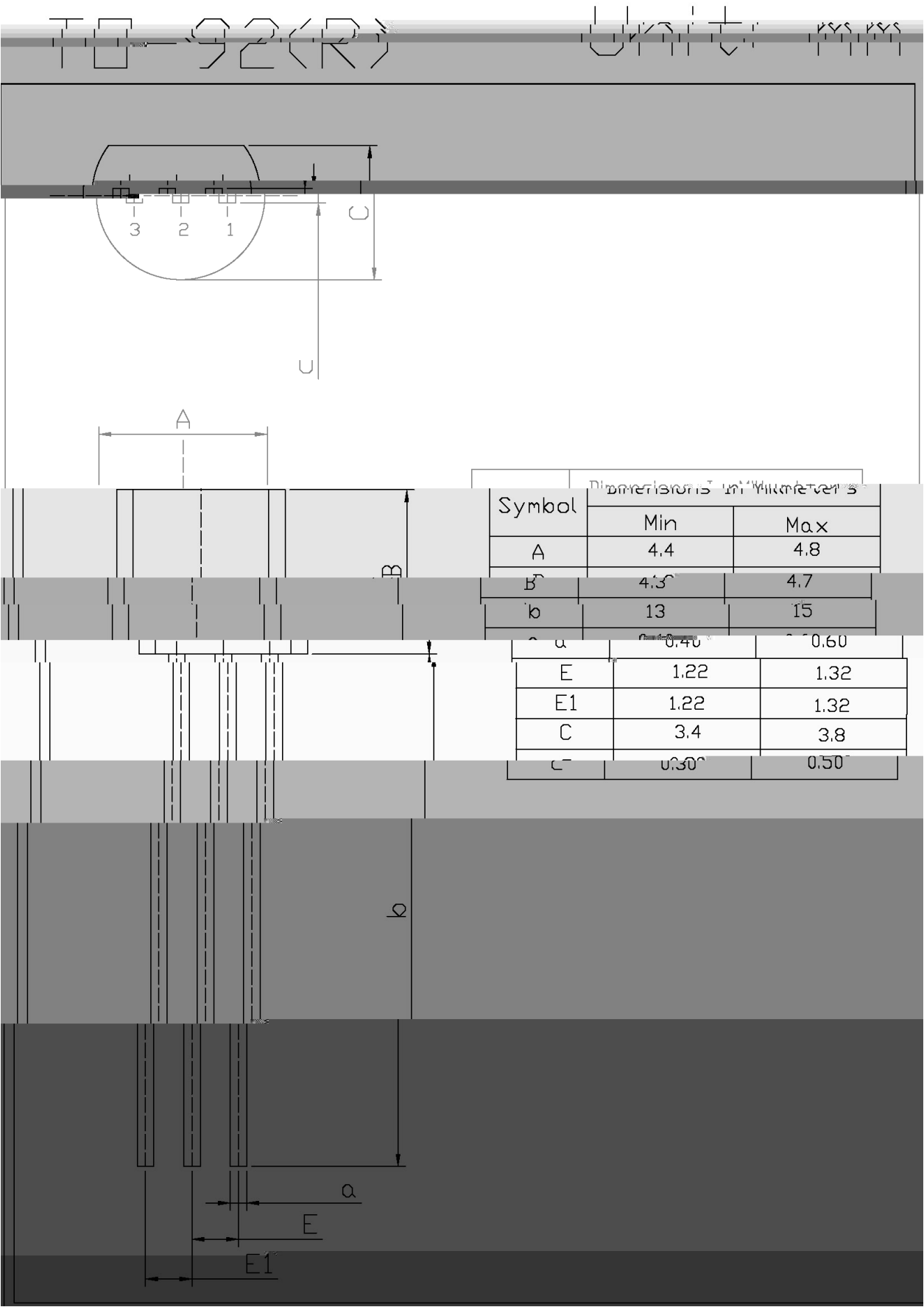
PIN1 χ Emitter

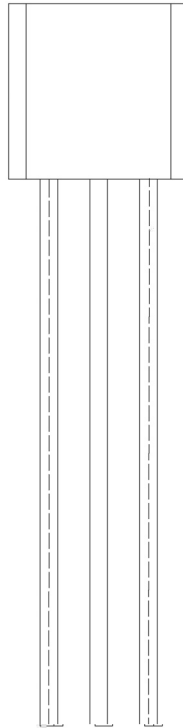
PIN 2 χ

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-65	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Emitter Current - Continuous	I_E	100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -30V$ $I_E = 0$			-0.015	μA









б " X

1. $\dot{\gamma}$ 25 K 150 t i 'H j 60 K 90sec;
2. $\ddot{\gamma}$ 255 ° 5 t i 'H j 'Y A K 5 ° 0.5sec;
3. i ' Y, o h y K 2 K 10 t /sec.

Note:

1. Preheating: 25~150 t , Time: 60~90sec.
2. Peak Temp.: 255 ° 5 t , Duration: 5 ° 0.5sec.
3. Cooling Speed: 2~10 t /sec.

$\dot{\gamma}$ X 270 ° 5 t

'H j X 10 ° 1 sec.

Temp.: 270±5

Time: 10±1 sec

“Q T Y E / BULK

Package Type	Units					Dimension (unit mm3)		
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

“V Y E / AMMO

Package Type	Units					Dimension (unit mm3)	
	Units/tape /	Tape/Inner Box /	Rows/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Inner Box	Outer Box
TO-92	3,000	1	120	10	30,000	328×230×42	480×346×235 547×407×268